
2SB738, 2SB739

Silicon PNP Epitaxial

HITACHI

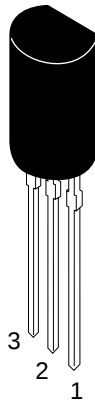
ADE-208-1030 (Z)
1st. Edition
Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SD787 and 2SD788

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SB738, 2SB739

Absolute Maximum Ratings (Ta = 25°C)

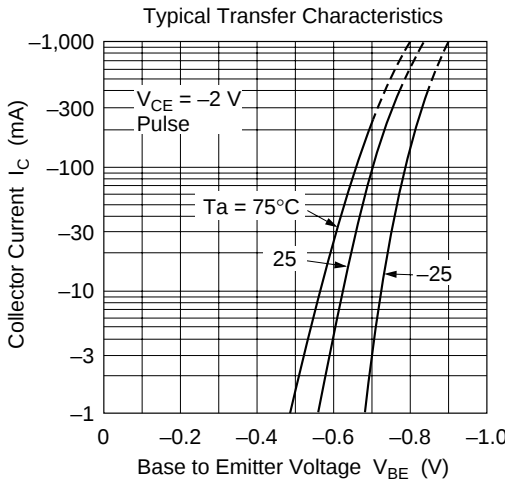
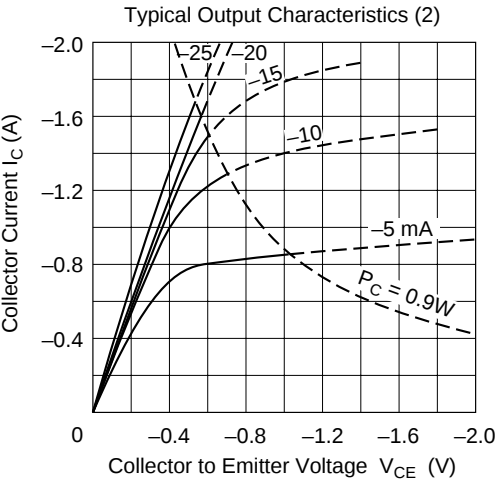
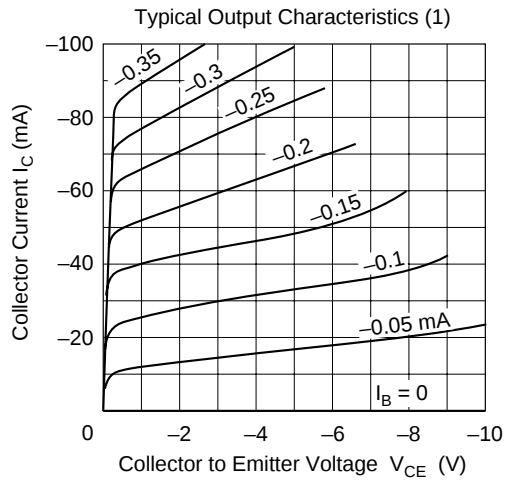
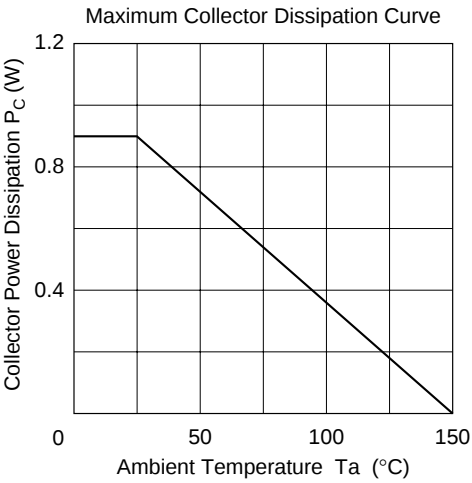
Item	Symbol	2SB738	2SB739	Unit
Collector to base voltage	V_{CBO}	-20	-20	V
Collector to emitter voltage	V_{CEO}	-16	-20	V
Emitter to base voltage	V_{EBO}	-6	-6	V
Collector current	I_C	-2	-2	A
Collector power dissipation	P_C	0.9	0.9	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

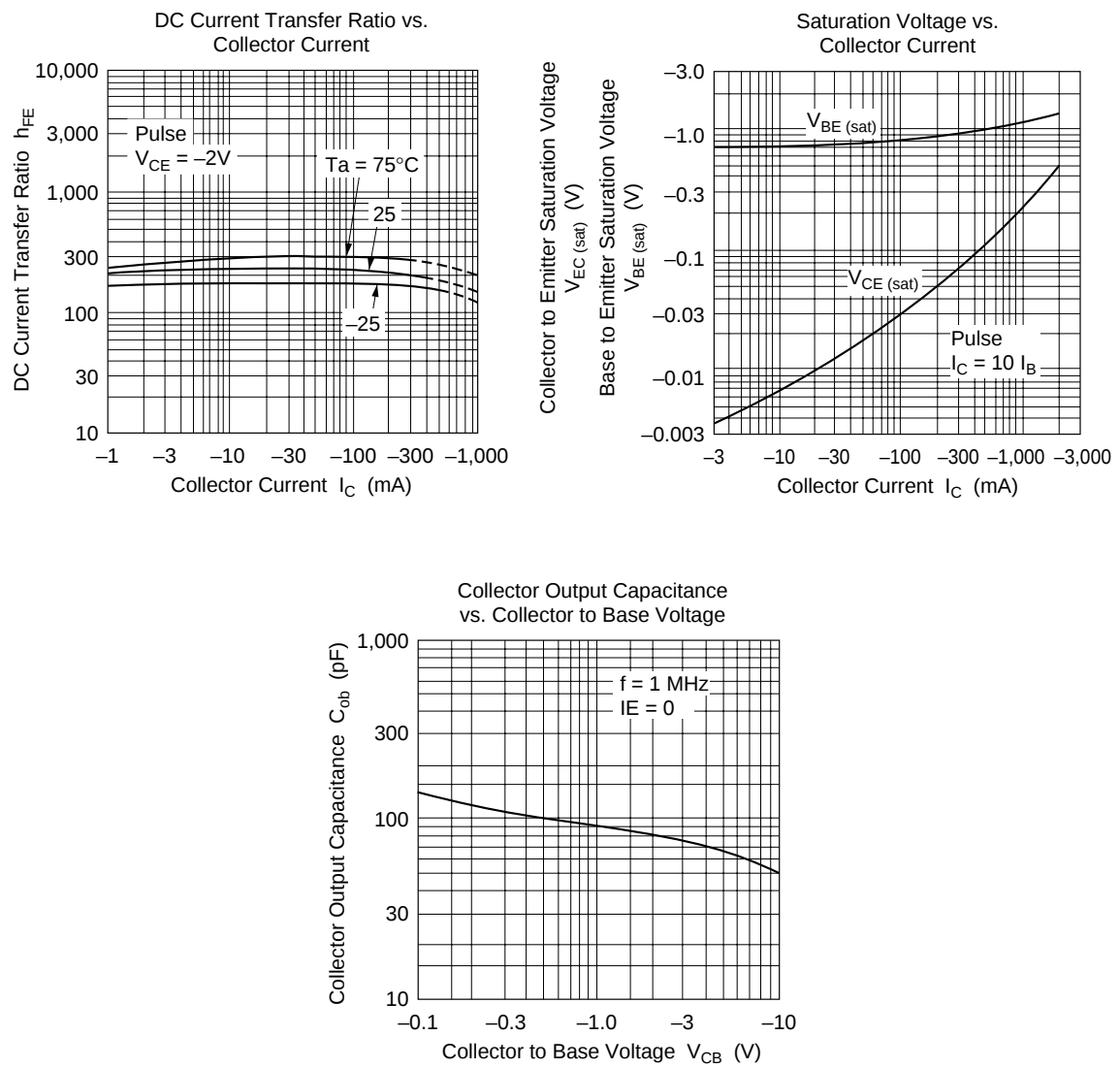
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB738			2SB739			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-20	—	—	-20	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-16	—	—	-20	—	—	V	$I_C = -1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	-6	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-2	—	—	-2	μA	$V_{CB} = -16\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.2	—	—	-0.2	μA	$V_{EB} = -6\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	320	100	—	320		$V_{CE} = -2\text{ V}$, $I_C = -0.1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.3	—	—	-0.3	V	$I_C = -1\text{ A}$, $I_B = -0.1\text{ A}$
Gain bandwidth product	f_T	—	150	—	—	150	—	MHz	$V_{CE} = -2\text{ V}$, $I_C = -10\text{ mA}$
Collector output capacitance	C_{ob}	—	50	—	—	50	—	pF	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: 1. The 2SB738 and 2SB739 are grouped by h_{FE} as follows.

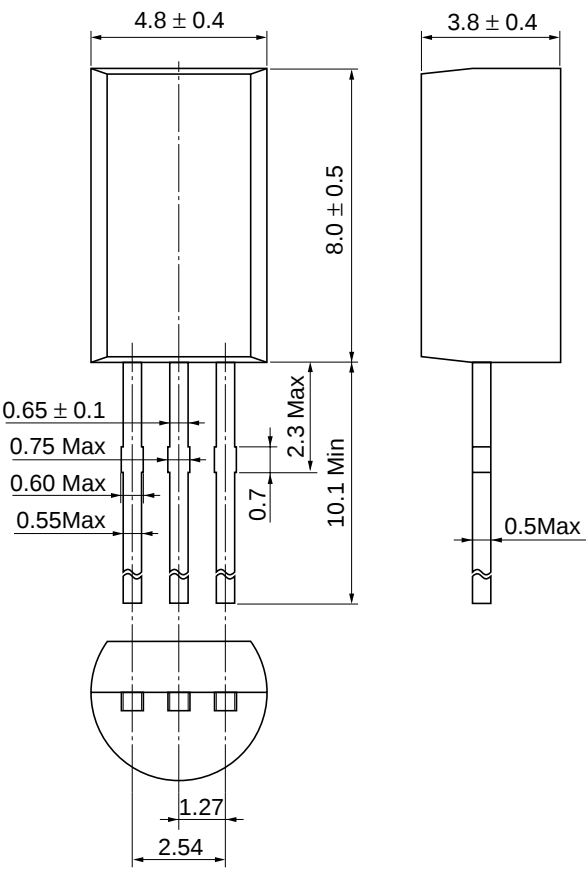
B	C
100 to 200	160 to 320





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.35 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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